

## **STD15NF10**

# N-channel 100 V, 0.060 Ω, 23 A, DPAK low gate charge STripFET™ II Power MOSFET

#### **Features**

Туре	V <sub>DSSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STD15NF10	100 V	< 0.065 Ω	23 A

- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

### **Application**

■ Switching applications

#### **Description**

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency, high-frequency isolated DC-DC converters for telecom and computer applications. It is also intended for any applications with low gate drive requirements.

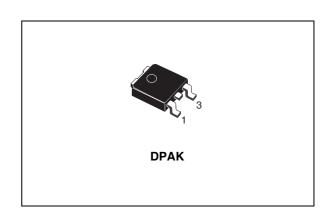


Figure 1. Internal schematic diagram

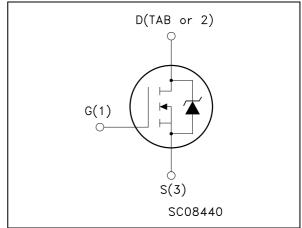


Table 1. Device summary

Order code	Marking	Package	Packaging
STD15NF10T4	D15NF10	DPAK	Tape and reel

Contents STD15NF10

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STD15NF10 Electrical ratings

# 1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source voltage (V <sub>GS</sub> = 0)	100	V
V <sub>DGR</sub>	Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )	100	٧
V <sub>GS</sub>	Gate-source voltage	± 20	V
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> = 25 °C	23	Α
I <sub>D</sub>	Drain current (continuous) at T <sub>C</sub> =100 °C	16	Α
I <sub>DM</sub> <sup>(1)</sup>	Drain current (pulsed)	92	Α
P <sub>TOT</sub>	Total dissipation at $T_C = 25$ °C	70	
	Derating factor	0.46	
E <sub>AS</sub> (2)	Single pulse avalanche energy	180	mJ
dv/dt (3)	Peak diode recovery voltage slope	9	
T <sub>stg</sub>	Storage temperature	-55 to 175	
$T_J$	Max. operating junction temperature	-55 to 175	

<sup>1.</sup> Pulse width limited by safe operating area

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R <sub>thJC</sub>	Thermal resistance junction-case max	2.14	°C/W
R <sub>thJA</sub>	Thermal resistance junction-ambient max	100	°C/W
T <sub>I</sub>	Maximum lead temperature for soldering purpose	300	°C

5/

<sup>2.</sup> Starting  $T_J = 25$  °C,  $I_D = 10A$ ,  $V_{DD} = 30V$ 

<sup>3.</sup>  $I_{SD} \leq$  13 A, di/dt  $\leq$  300 A/ $\mu$ s,  $V_{DS} \leq$   $V_{(BR)DSS}$ ,  $T_{J} \leq$   $T_{JMAX}$ 

Electrical characteristics STD15NF10

# 2 Electrical characteristics

(T<sub>CASE</sub> = 25 °C unless otherwise specified)

Table 4. On<sup>(1)</sup> /off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
I <sub>DSS</sub>	Zero gate voltage drain current (V <sub>GS</sub> = 0)	$V_{DS}$ = Max rating $V_{DS}$ = Max rating,@ 125 °C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSS</sub>	Gate body leakage current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 20 V			±100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	٧
R <sub>DS(on)</sub>	Static drain-source on resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12 A		0.06	0.065	Ω

<sup>1.</sup> Pulsed: Pulse duration = 300  $\mu$ s, duty cycle 1.5%

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g <sub>fs</sub> <sup>(1)</sup>	Forward transconductance	$V_{DS} = 15 V_{,} I_{D} = 7.5 A$		12		S
C <sub>iss</sub> C <sub>oss</sub> C <sub>rss</sub>	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25 \text{ V, f} = 1 \text{ MHz,}$ $V_{GS} = 0$		870 125 50		pF pF pF
Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub>	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 80 \text{ V}, I_{D} = 24 \text{ A}$ $V_{GS} = 10 \text{ V}$		30 6 10	40	nC nC nC

<sup>1.</sup> Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
$\begin{array}{c} t_{d(on)} \\ t_{r} \\ t_{d(off)} \\ t_{f} \end{array}$	Turn-on delay time Rise time Turn-off delay time Fall time	$V_{DD}$ = 50 V, $I_{D}$ = 12 A, $R_{G}$ = 4.7 $\Omega$ , $V_{GS}$ = 10 V Figure 13 on page 8		60 45 49 17		ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I <sub>SD</sub>	Source-drain current				23	Α
I <sub>SDM</sub> <sup>(1)</sup>	Source-drain current (pulsed)				92	Α
V <sub>SD</sub> <sup>(2)</sup>	Forward on voltage	$I_{SD} = 20 \text{ A}, V_{GS} = 0$			1.5	٧
t <sub>rr</sub> Q <sub>rr</sub> I <sub>RRM</sub>	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD}$ = 24 A, di/dt = 100 A/ $\mu$ s, $V_{DD}$ = 30 V, $T_{J}$ = 150 °C Figure 15 on page 8		100 375 7.5		ns nC A

<sup>1.</sup> Pulse width limited by safe operating area.

<sup>2.</sup> Pulsed: pulse duration = 300  $\mu$ s, duty cycle 1.5%

Electrical characteristics STD15NF10

### 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

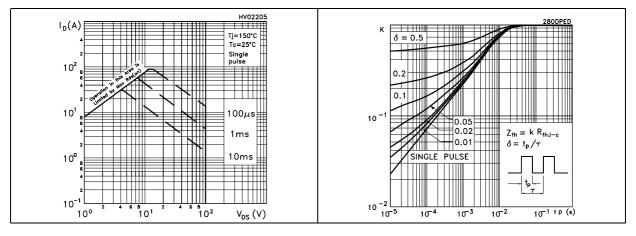


Figure 4. Output characteristics

Figure 5. Transfer characteristics

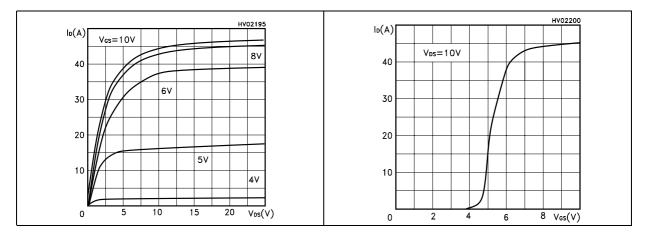


Figure 6. Transconductance

Figure 7. Static drain-source on resistance

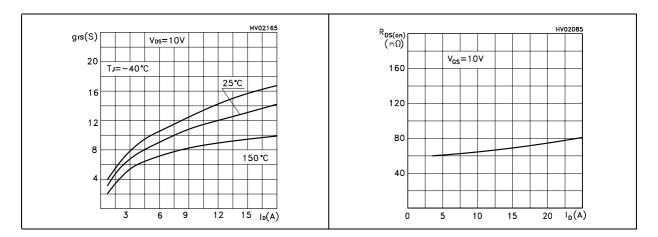
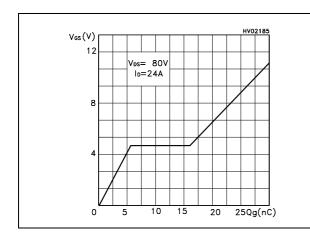


Figure 8. Gate charge vs. gate-source voltage Figure 9. Capacitance variations



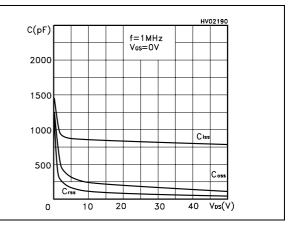
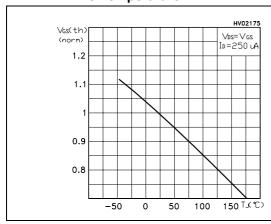


Figure 10. Normalized gate threshold voltage vs. temperature

Figure 11. Normalized on resistance vs. temperature



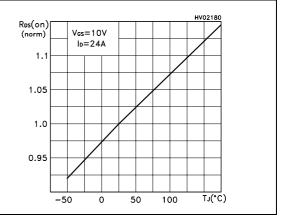
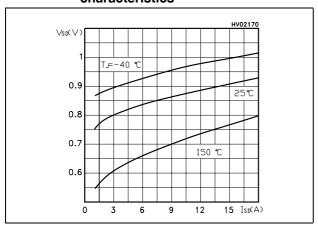


Figure 12. Source-drain diode forward characteristics



Test circuit STD15NF10

## 3 Test circuit

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

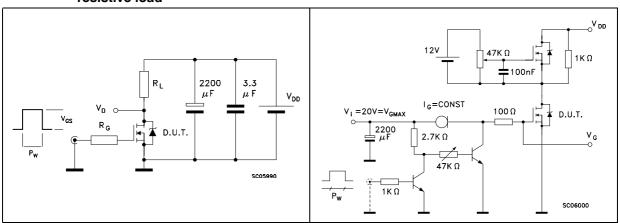


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

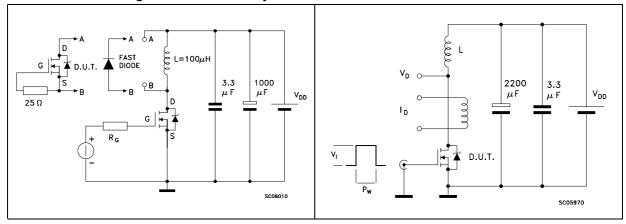
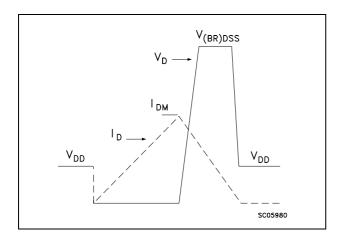


Figure 17. Unclamped inductive waveform

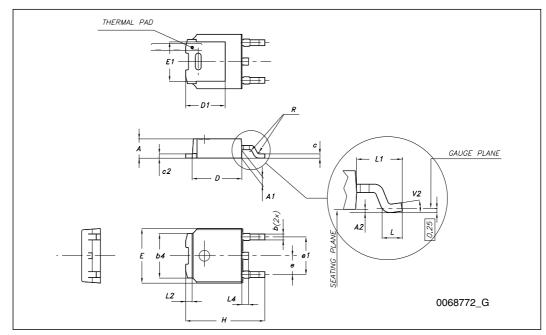


# 4 Package mechanical data

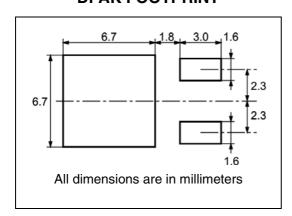
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

### TO-252 (DPAK) mechanical data

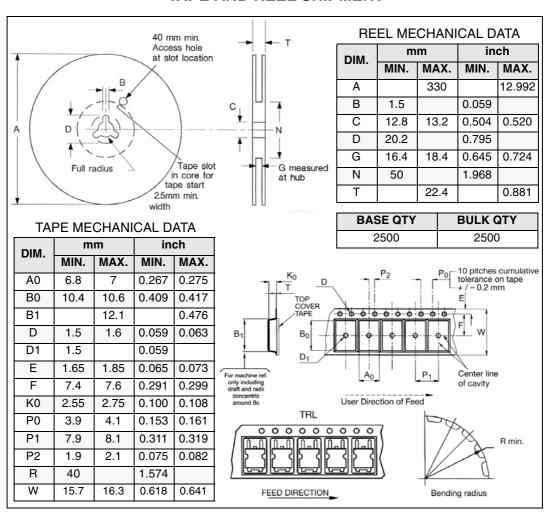
DIM.		mm.	
DIIVI.	min.	typ	max.
А	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
е		2.28	
e1	4.40		4.60
Н	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °



# 5 Packaging mechanical data DPAK FOOTPRINT



#### TAPE AND REEL SHIPMENT



Revision history STD15NF10

# 6 Revision history

Table 8. Revision history

Date	Revision	Changes
21-Jun-2004	3	No history because migration.
09-Sep-2004	4	Complete document
08-Aug-2006	5	New template, updated SOA
04-Nov-2008	6	Q <sub>G</sub> max value in <i>Table 5</i> has been corrected.

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